### **ON Semiconductor**

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### **BS107A**

## **Small Signal MOSFET**

250 mA, 200 V, N-Channel TO-92

#### **Features**

- AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain – Source Voltage	V <sub>DS</sub>	200	Vdc
Gate–Source Voltage  – Continuous  – Non–repetitive (t <sub>p</sub> ≤ 50 μs)	V <sub>GS</sub> V <sub>GSM</sub>	±20 ±30	Vdc Vpk
Drain Current Continuous (Note 1) Pulsed (Note 2)	I <sub>D</sub>	250 500	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	350	mW
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

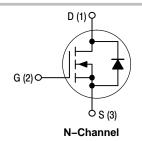
- The Power Dissipation of the package may result in a lower continuous drain current.
- 2. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

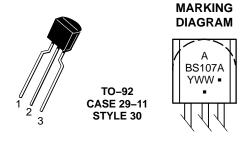


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# 250 mAMPS, 200 VOLTS $R_{DS(on)} = 6.4 \Omega$





A = Assembly Location

Y = Year WW = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

Device	Package	Shipping
BS107ARL1G	TO-92 (Pb-Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			-		•
Zero-Gate-Voltage Drain Current (V <sub>DS</sub> = 130 Vdc, V <sub>GS</sub> = 0)	I <sub>DSS</sub>	-	-	30	nAdc
Drain-Source Breakdown Voltage ( $V_{GS} = 0$ , $I_D = 100 \mu Adc$ )	V <sub>(BR)DSX</sub>	200	-	-	Vdc
Gate Reverse Current (V <sub>GS</sub> = 15 Vdc, V <sub>DS</sub> = 0)	I <sub>GSS</sub>	_	0.01	10	nAdc
ON CHARACTERISTICS (Note 3)					
Gate Threshold Voltage (I <sub>D</sub> = 1.0 mAdc, V <sub>DS</sub> = V <sub>GS</sub> )	V <sub>GS(Th)</sub>	1.0	_	3.0	Vdc
Static Drain–Source On Resistance BS107 ( $V_{GS} = 2.6$ Vdc, $I_D = 20$ mAdc) ( $V_{GS} = 10$ Vdc, $I_D = 200$ mAdc) BS107A ( $V_{GS} = 10$ Vdc) ( $I_D = 100$ mAdc) ( $I_D = 250$ mAdc)	r <sub>DS(on)</sub>	-	- - 4.5 4.8	28 14 6.0 6.4	Ω
SMALL-SIGNAL CHARACTERISTICS			1	1	<u>I</u>
Input Capacitance (V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>iss</sub>	-	60	_	pF
Reverse Transfer Capacitance (V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>rss</sub>	-	6.0	-	pF
Output Capacitance (V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>oss</sub>	-	30	-	pF
Forward Transconductance (V <sub>DS</sub> = 25 Vdc, I <sub>D</sub> = 250 mAdc)	9 <sub>fs</sub>	200	400	-	mmhos
SWITCHING CHARACTERISTICS		_	_	_	_
Turn-On Time	t <sub>on</sub>	-	6.0	15	ns
Turn-Off Time	t <sub>off</sub>	_	12	15	ns

<sup>3.</sup> Pulse Test: Pulse Width  $\leq 300 \,\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

### **RESISTIVE SWITCHING**

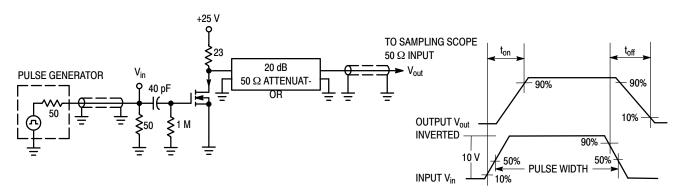
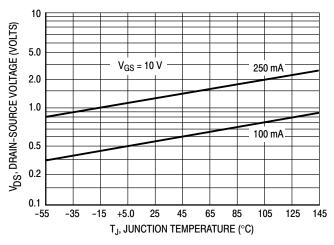
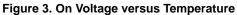


Figure 1. Switching Test Circuit

Figure 2. Switching Waveforms

### **BS107A**





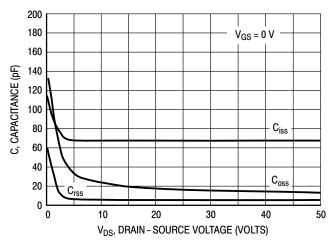


Figure 4. Capacitance Variation

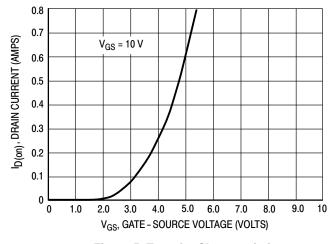


Figure 5. Transfer Characteristic

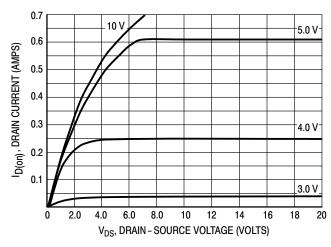


Figure 6. Output Characteristic

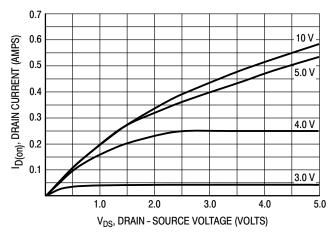
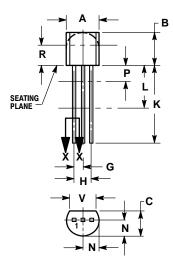


Figure 7. Saturation Characteristic

### **BS107A**

#### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM

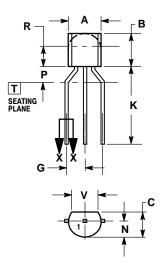


STRAIGHT LEAD **BULK PACK** 



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  CONTOUR OF PACKAGE BEYOND DIMENSION R
  IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



**BENT LEAD TAPE & REEL** AMMO PACK



#### NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
  CONTOUR OF PACKAGE BEYOND
  DIMENSION R IS UNCONTROLLED.

- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN MAX		
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
Р	1.50	4.00	
R	2.93		
٧	3.43		

STYLE 30: PIN 1. DRAIN GATE 2. SOURCE

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